

ABSTRACT OF THE DISCLOSURE

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5 The semiconductor device according to the present invention comprises a V-groove having V-shaped cross-section formed on a semiconductor substrate or on an epitaxial growth layer grown on a semiconductor substrate, and an active layer is provided only at the bottom of said V-groove. The method for manufacturing a semiconductor device according to the present invention comprises the steps of forming a stripe-like etching protective film in  
10 <011> direction of a semiconductor substrate or an epitaxial growth layer grown on it, performing gas etching using hydrogen chloride as etching gas on a semiconductor substrate or on an epitaxial growth layer grown on a semiconductor substrate to form a V-groove, and forming an  
15 active layer at the bottom of said V-groove.

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